查询FG3000DV-90DA供应商

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MITSUBISHI GATE TURN-OFF THYRISTORS

FG3000DV-90DA

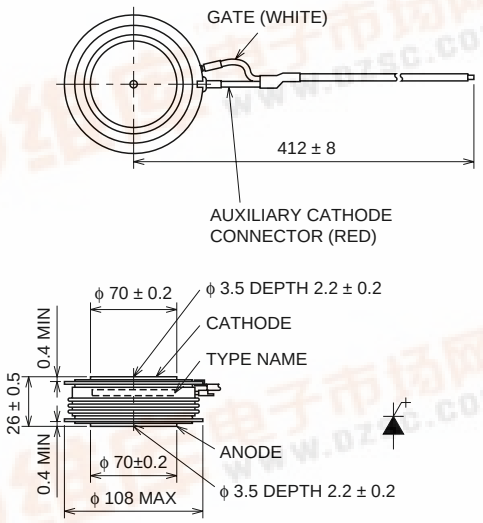
HIGH POWER INVERTER USE
PRESS PACK TYPE

FG3000DV-90DA

- I_{TQRM} Repetitive controllable on-state current 3000A
- $I_{T(AV)}$ Average on-state current 950A
- V_{DRM} Repetitive peak off state voltage 4500V
- Anode short type

OUTLINE DRAWING

Dimensions in mm



APPLICATION

Inverters, D.C. choppers, Induction heaters, D.C. to D.C. converters.

MAXIMUM RATINGS

Symbol	Parameter	Voltage class	Unit
		90DA	
V_{RRM}	Repetitive peak reverse voltage	17	V
V_{RSM}	Non-repetitive peak reverse voltage	17	V
$V_{R(DC)}$	DC reverse voltage	17	V
V_{DRM}	Repetitive peak off-state voltage*	4500	V
V_{DSM}	Non-repetitive peak off-state voltage*	4500	V
$V_{D(DC)}$	DC off-state voltage*	2500	V

* : V_{GK} = –2V

Symbol	Parameter	Conditions	Ratings	Unit
I_{TQRM}	Repetitive controllable on-state current	V_{DM} = 3375V, T_j = 125°C, C_S = 6.0μF, L_S = 0.3μH	3000	A
$I_{T(RMS)}$	RMS on-state current		1490	A
$I_{T(AV)}$	Average on-state current	f = 60Hz, sine wave θ = 180°, T_f = 71°C	950	A
I_{TSM}	Surge (non-repetitive) on-state current	One half cycle at 60Hz	17	kA
I^2t	Current-squared, time integration	One cycle at 60Hz	1.2×10^6	A^2s
di_T/dt	Critical rate of rise of on-state current	V_D = 2250V, I_{GM} = 40A, T_j = 125°C	500	A/μs
V_{FGM}	Peak forward gate voltage		10	V
V_{RGM}	Peak reverse gate voltage		17	V
I_{FGM}	Peak forward gate current		100	A
I_{RGM}	Peak gate reverse current		900	A
P_{FGM}	Peak forward gate power dissipation		400	W
P_{RGM}	Peak reverse gate power dissipation		27	kW
$P_{FG(AV)}$	Average forward gate power dissipation		100	W
$P_{RG(AV)}$	Average reverse gate power dissipation		230	W
T_j	Junction temperature		–40 ~ +125	°C
T_{stg}	Storage temperature		–40 ~ +150	°C
—	Mounting force required	Recommended value 33	30 ~ 40	kN
—	Weight	Standard value	1220	g

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FG3000DV-90DA

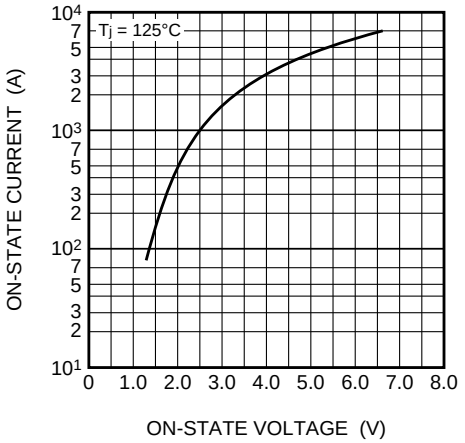
HIGH POWER INVERTER USE
PRESS PACK TYPE

ELECTRICAL CHARACTERISTICS

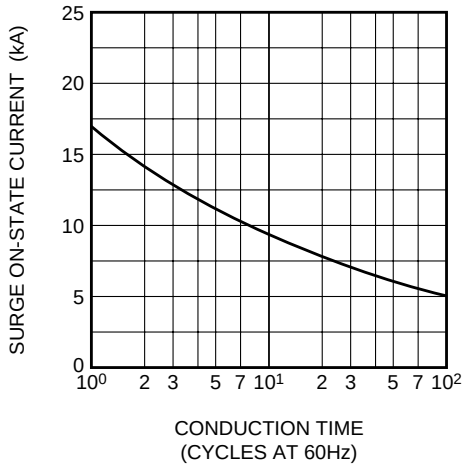
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V_{TM}	On-state voltage	T_j = 125°C, I_{TM} = 3000A, Instantaneous measurment	—	—	4.0	V
I_{RRM}	Repetitive peak reverse current	T_j = 125°C, V_{RRM} Applied	—	—	300	mA
I_{DRM}	Repetitive peak off-state current	T_j = 125°C, V_{DRM} Applied, V_{GK} = –2V	—	—	150	mA
I_{RG}	Reverse gate current	T_j = 125°C, V_{RG} = 17V	—	—	300	mA
dv/dt	Critical rate of rise of off-state voltage	T_j = 125°C, V_D = 2250V, V_{GK} = –2V	1000	—	—	V/µs
t_{gt}	Turn-on time	T_j = 125°C, I_{TM} = 3000A, I_{GM} = 40A, V_D = 2250V	—	—	10	µs
t_{gq}	Turn-off time	T_j = 125°C, I_{TM} = 3000A, V_{DM} = 3375V, di_{GQ}/dt = –40A/µs V_{RG} = 17V, C_S = 6.0µF, L_S = 0.3µH	—	—	30	µs
I_{GQM}	Peak gate turn-off current		—	670	—	A
V_{GT}	Gate trigger voltage	DC METHOD : V_D = 24V, R_L = 0.1Ω, T_j = 25°C	—	—	1.5	V
I_{GT}	Gate trigger current		—	—	4000	mA
$R_{th(j-f)}$	Thermal resistance	Junction to fin	—	—	0.015	°C/W

PERFORMANCE CURVES

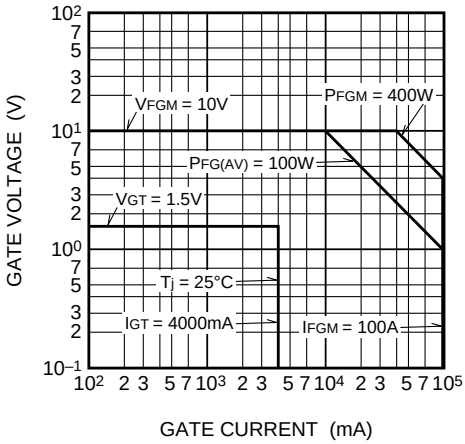
MAXIMUM ON-STATE CHARACTERISTIC



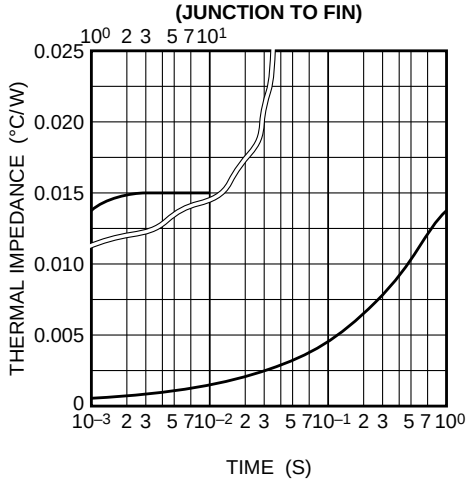
RATED SURGE ON-STATE CURRENT



GATE CHARACTERISTICS

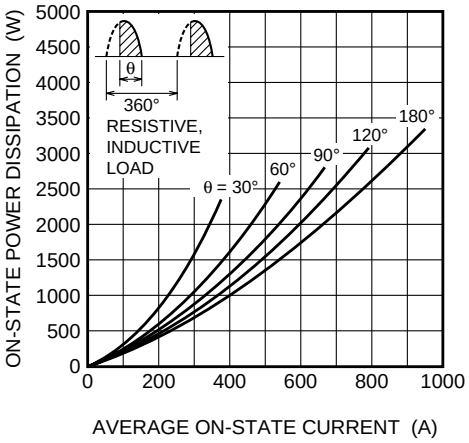


MAXIMUM THERMAL IMPEDANCE CHARACTERISTIC (JUNCTION TO FIN)

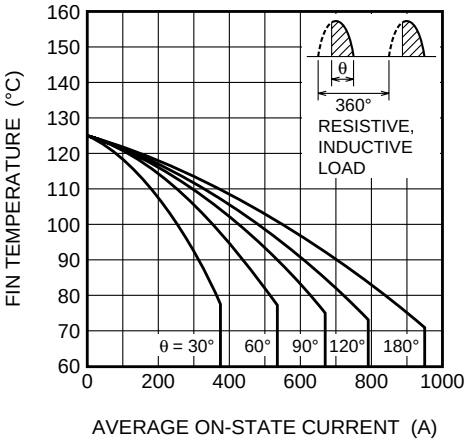


MITSUBISHI ELECTRIC

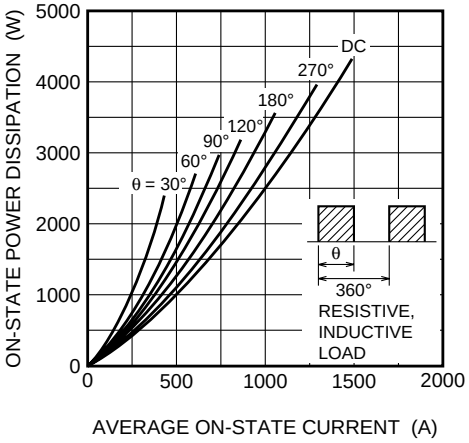
MAXIMUM ON-STATE POWER DISSIPATION CHARACTERISTICS (SINGLE-PHASE HALF WAVE)



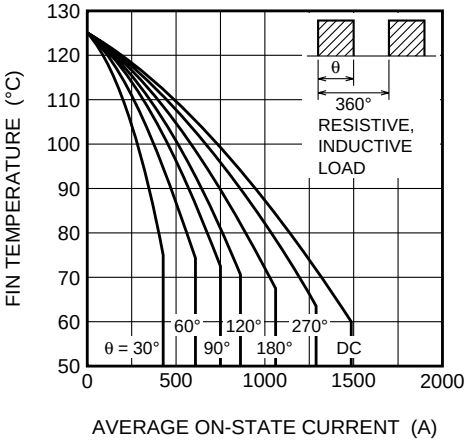
ALLOWABLE FIN TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE HALF WAVE)



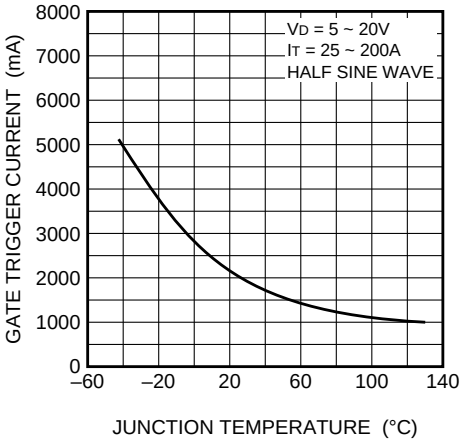
MAXIMUM ON-STATE POWER DISSIPATION CHARACTERISTICS (RECTANGULAR WAVE)



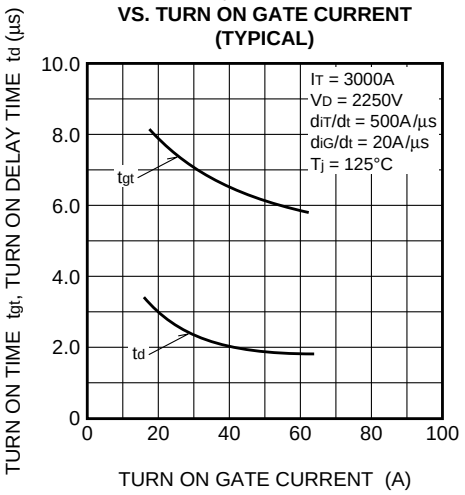
ALLOWABLE FIN TEMPERATURE VS. AVERAGE ON-STATE CURRENT (RECTANGULAR WAVE)



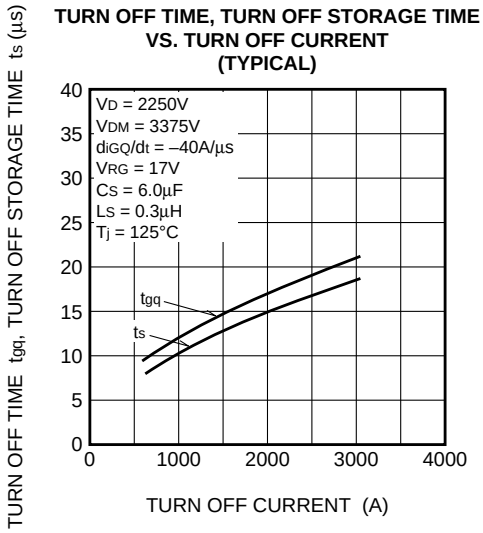
GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE (TYPICAL)



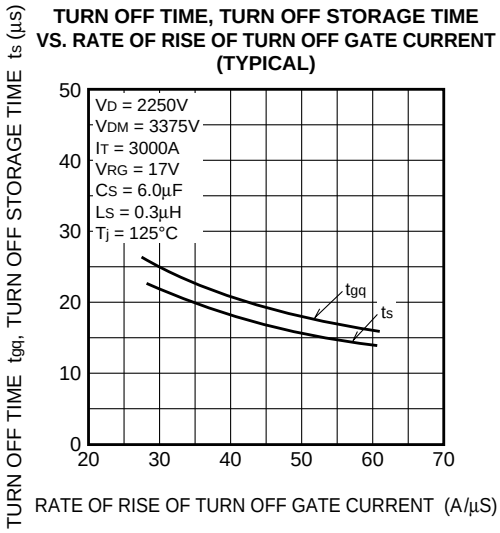
TURN ON TIME, TURN ON DELAY TIME VS. TURN ON GATE CURRENT (TYPICAL)



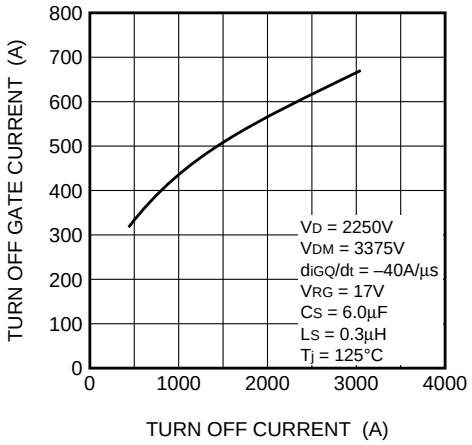
TURN OFF TIME, TURN OFF STORAGE TIME VS. TURN OFF CURRENT (TYPICAL)



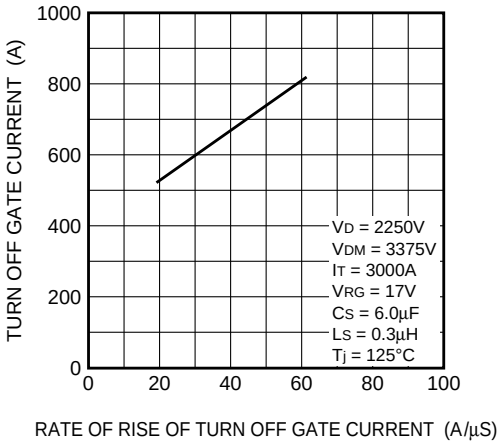
TURN OFF TIME, TURN OFF STORAGE TIME VS. RATE OF RISE OF TURN OFF GATE CURRENT (TYPICAL)



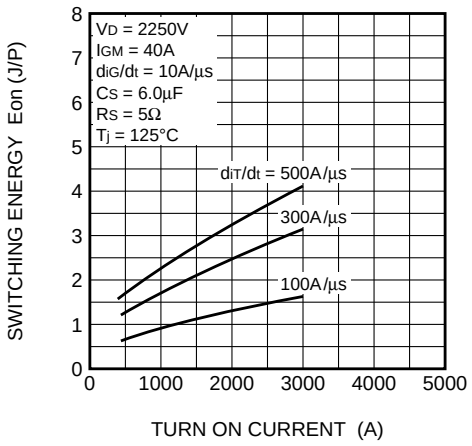
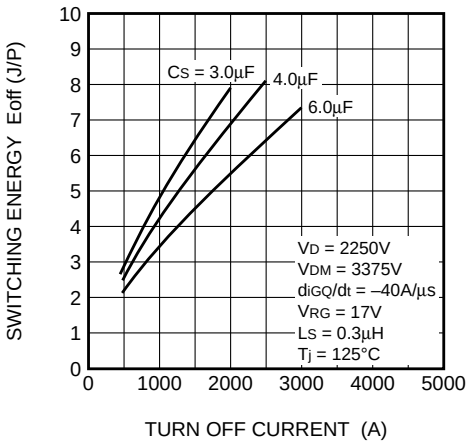
TURN OFF GATE CURRENT VS. TURN OFF CURRENT (TYPICAL)



TURN OFF GATE CURRENT VS. RATE OF RISE OF GATE CURRENT (TYPICAL)



TURN ON SWITCHING ENERGY (MAXIMUM)



TURN OFF SWITCHING ENERGY (MAXIMUM)